

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	66	(nmos mos mosfet) same thick same native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 11:28
L2	14	1 same (capacit\$5 stor\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 11:35
L30	52	thick same native same leak\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 13:09
L31	15	thick same native same (esd electro (electro adj static))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:20
L32	129	thick same native same protect\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 13:11
L33	24	32 same (capacit\$5 stor\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 13:12
L34	0	advantage adj of adj mos adj capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 13:53
L35	123	advantage with (mos adj capacitors)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 13:54
L36	54	advantage\$5 near3 (mos adj capacitors)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 14:25
L37	17	ESD same (trigger adj FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 14:33
L38	22	ESD same trigger same nmos same rc	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:06

L39	198	ker-ming-dou.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:08
L40	105	ker-ming-dou.in. and esd.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:06
L41	20	40 and chang-hun-hsien.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:07
L42	4	ker-ming-dou.in. and native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:10
L43	4	hu-chang-fen.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 15:10
L44	250	(gate adj oxide) same angstrom same leak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:20
L45	2	44 same (esd electro (electro adj static))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:20
L46	17	44 and (esd electro (electro adj static))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:21
S1	2420	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:20
S2	22883	(esd (((electro adj static) electrostatic) adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 15:51
S3	456219	(rc (resistor and capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 15:52

S4	1438	S2 same (rc (resistor and capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 15:53
S5	132389	native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 15:53
S6	1305	S2 same (rc (resistor same capacitor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:10
S7	5	S5 same S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 15:53
S8	50	S2 same S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:10
S9	10	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:45
S10	4368	capacit\$4 same native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:45
S11	8	S2 same S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:46
S12	161710	capacit\$4 with (gate oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:48
S13	965	S2 same S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:48
S14	3	S13 same native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:47

S15	278	S1 and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:48
S16	11029	capacit\$4 with gate with oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:48
S17	101	S2 same S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/23 17:48
S18	38	S1 and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:11
S19	1048	native same leak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:23
S20	2422	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:12
S21	2	S19 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:33
S22	22925	(esd (((electro adj static) electrostatic) adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:06
S23	1	S19 same S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:13
S24	158	S19 same capacit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:28
S25	36	S24 same (transistor \$3mos mos\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:05

S26	1	S25 and (esd (((electro adj static) electrostatic) adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:26
S27	2	S24 and (esd (((electro adj static) electrostatic) adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:26
S28	10	S24 same protect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:28
S29	1	S25 same thick	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:31
S30	5	S25 same thick\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 12:31
S31	5592	mos adj capacit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:02
S32	133	S31 same (thick near3 (native gate oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 13:35
S33	381	S31 same leak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 13:36
S34	9	S32 same S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 13:36
S35	59335	capacit\$4 same (thick\$3 thin\$3 near (native gate oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:03
S36	3617	S35 same leak\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:03

S37	1185	S36 same (transistor \$3mos mos\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:06
S38	212	S35 same (esd (((electro adj static) electrostatic) adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:06
S39	147	S38 same (transistor \$3mos mos\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/26 16:19
S40	13	S38 same S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 14:07
S41	136	S39 not S40 not S34 not S27 not S28 not S30 not S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/24 16:24
S42	2	("6552886").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/24 16:24
S43	569	thick with native	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:33
S44	397	S43 with (gate oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:34
S45	5	S44 with (capacit\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:36
S46	13	(S43 with (capacit\$5)) not S45	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:37
S47	17	S43 with (transistor \$2mos mos\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/25 12:38